



STW45NM50

N-CHANNEL 500V - 0.07Ω - 45A TO-247

MDmesh™ Power MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW45NM50	500V	<0.09Ω	45 A

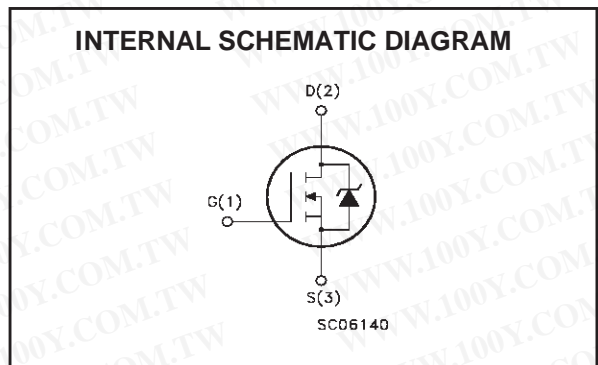
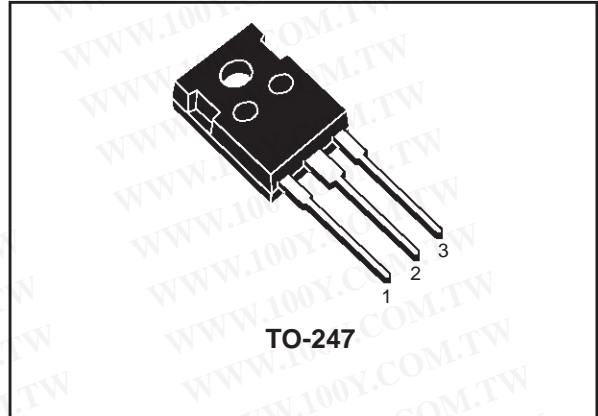
- TYPICAL R_{DS(on)} = 0.07Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS

DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	500	V
V _{GS}	Gate- source Voltage	±30	V
I _D	Drain Current (continuous) at T _C = 25°C	45	A
I _D	Drain Current (continuous) at T _C = 100°C	28.4	A
I _{DM} (●)	Drain Current (pulsed)	180	A
P _{TOT}	Total Dissipation at T _C = 25°C	260	W
	Derating Factor	2.08	W/°C
dv/dt	Peak Diode Recovery voltage slope	6	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(●)Pulse width limited by safe operating area

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

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THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.48	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	30	°C/W
Rthc-sink	Thermal Resistance Case-sink	Typ	0.1	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	45	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	1400	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 22.5A		0.07	0.09	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} , V _{GS} = 10V	45			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 22.5A		25		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		4400		pF
C _{oss}	Output Capacitance			710		pF
C _{rss}	Reverse Transfer Capacitance			110		pF
R _G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.3		Ω

Note: 1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

ELECTRICAL CHARACTERISTICS (CONTINUED)
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 250V, I_D = 22.5A$		16		ns
t_r	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		8		ns
Q_g	Total Gate Charge	$V_{DD} = 400V, I_D = 45A,$ $V_{GS} = 10V$		100	135	nC
Q_{gs}	Gate-Source Charge			33		nC
Q_{gd}	Gate-Drain Charge			83		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 400V, I_D = 45A,$		14		ns
t_f	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5)		6		ns
t_c	Cross-over Time			13		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				45	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				180	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 45A, V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 45A, di/dt = 100A/\mu s,$		270		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 100V, T_j = 150^\circ C$ (see test circuit, Figure 5)		1.6		μC
I_{RRM}	Reverse Recovery Current			100		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by safe operating area.

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Fig. 1: Unclamped Inductive Load Test Circuit

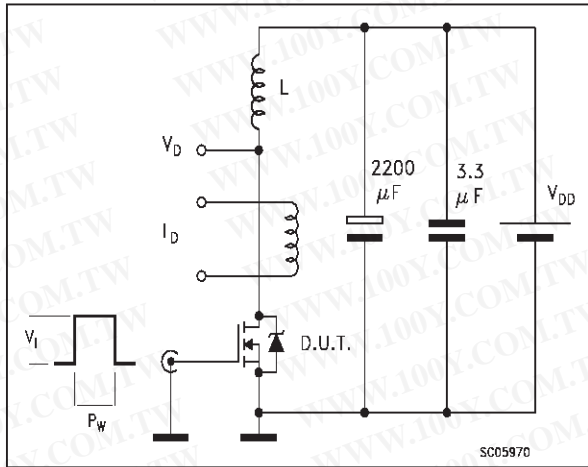


Fig. 2: Unclamped Inductive Waveform

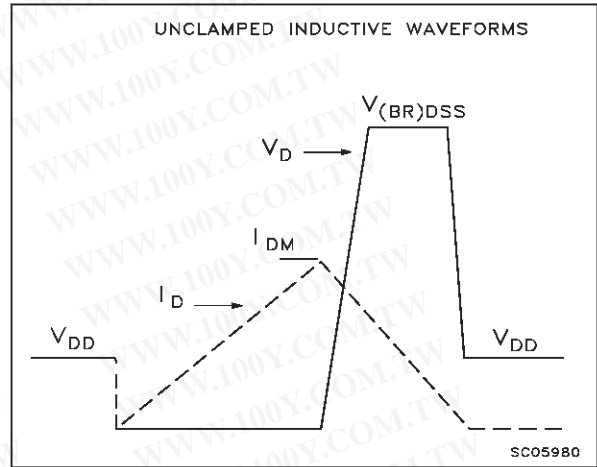


Fig. 3: Switching Times Test Circuit For Resistive Load

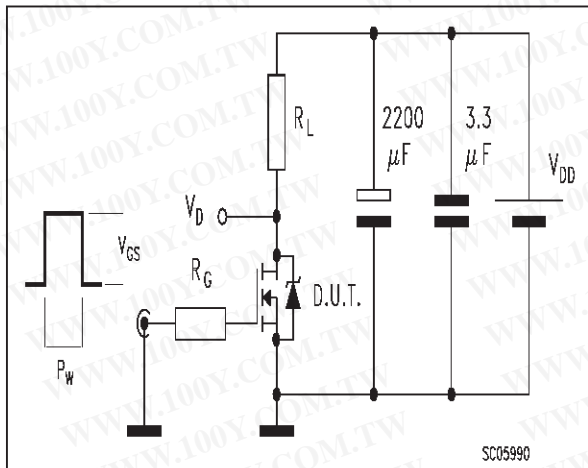


Fig. 4: Gate Charge test Circuit

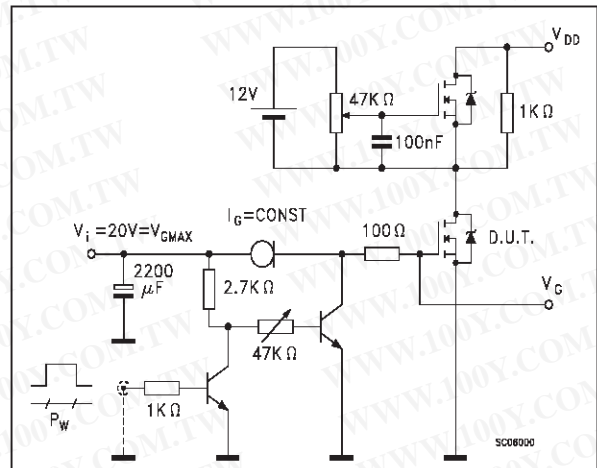
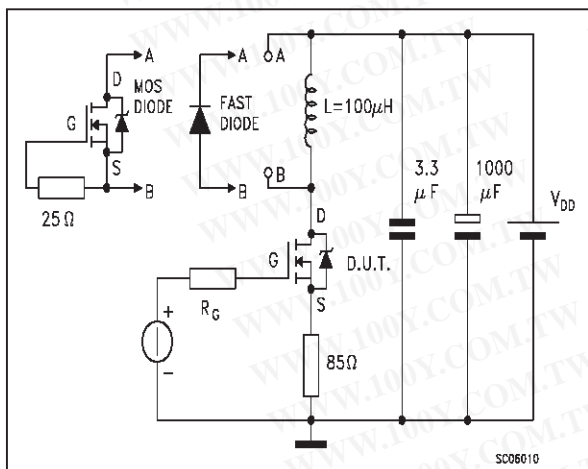


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118

